1



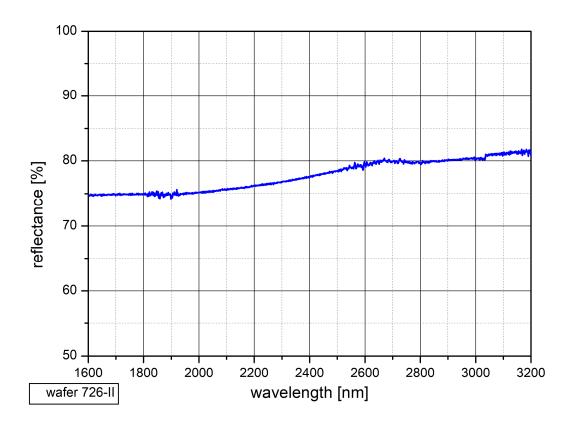
SAM™ Data Sheet SAM-2800-20-10ps-x, λ = 2800 nm

Laser wavelength	$\lambda = 2800 \text{ nm}$
High reflection band	λ = 2600 3200 nm
Absorbance	A ₀ = 20 %
Modulation depth	∆R = 12 %
Non-saturable loss	A _{ns} = 8 %
Saturation fluence	Φ_{sat} = 70 µJ/cm ²
Relaxation time constant	τ ~ 10 ps
Damage threshold	$\Phi = 1 \text{ mJ/cm}^2$
Chip area	4.0 mm x 4.0 mm; other dimensions on request
Chip thickness	625 µm
Reverse design	The laser beam is supplied through the AR coated GaAs substrate
	Please see figure below on page 2

Mounting option **x** denotes the type of mounting as follows:

x = 0	unmounted
x = 12.7 g	glued on a gold plated Cu-cylinder with 12.7 mm \varnothing
x = 25.4 g	glued on a gold plated Cu-cylinder with 25.4 mm \varnothing

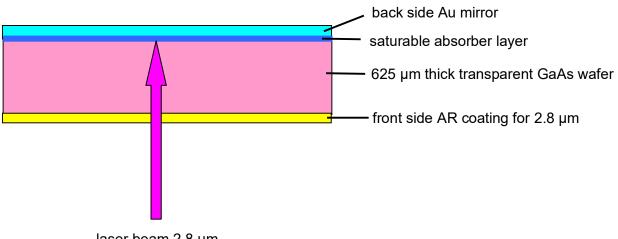
Low intensity spectral reflectance



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Reverse design of the SAM-2800-20-10ps-x



laser beam 2.8 µm